Ultra Low Phase Noise Amplifier 4 - 8 GHz



MAAL-011154

Rev. V2

Features

- Wideband Performance
- Phase Noise: -165 dBc/Hz @ 10 kHz Offset
- Noise Figure: 5 dB @ 5 GHz
- Bias Voltage: 5 V
- Bias Current: 85 mA
- 50 Ω Matched Input / Output
- Positive Voltage Only
- Lead-Free 4 mm 16-lead PQFN Package
- RoHS* Compliant

Applications

Test & Measurement, EW, ECM, and Radar

Description

The MAAL-011154 is an easy to use, wideband ultra low phase noise distributed amplifier in a lead-free 4 mm 16-lead PQFN package. It operates from 4 to 8 GHz and provides -165 dBc/Hz phase noise, 15.4 dB of linear gain, 19 dBm of P1dB, and 5 dB of noise figure. The input and output are fully matched to 50 Ω with typical return loss of 15 dB.

The RF output port is DC blocked. Amplifier control is available through the use of a control circuit.

This product is fabricated using a low phase noise HBT process which features full passivation for enhanced reliability.

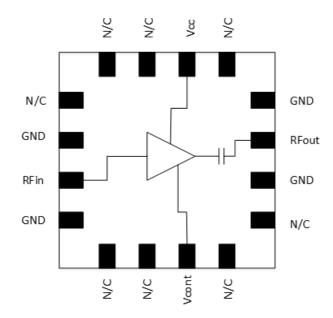
The MAAL-011154 can be used as a low noise amplifier stage for signal generation applications. This device is ideally suited for applications where ultra low phase noise and drive power is required.

Ordering Information^{1,2}

Part Number Package	
MAAL-011154-TR0100	100 piece reel
MAAL-011154-SMB	Sample Board

- 1. Reference Application Note M513 for reel size information.
- 2. All sample boards include 3 loose parts.

Functional Schematic



Pin Configuration

Pin #	Pin Name Description	
1,5,6,8,9,13,15,16	N/C ³	No Connection
2,4,10,12	GND	Ground
3	RF _{IN}	RF Input
7	V _{CONT}	Control Voltage
11	RF _{OUT}	RF Output
14	V _{CC}	Collector Voltage
Paddle ⁴	GND	Ground

- MACOM recommends connecting unused package pins to ground.
- The exposed pad centered on the package bottom must be connected to RF, DC and thermal ground.

^{*} Restrictions on Hazardous Substances, compliant to current RoHS EU directive.



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Electrical Specifications: Freq. = 4 - 8 GHz, T_A = +25°C, V_{CC} = +5 V, Z_0 = 50 Ω

Parameter	Test Conditions	Units	Min.	Тур.	Max.
Gain	P _{IN} = -15 dBm	dB	12.5	15.7	_
Gain Flatness	_	dB	_	±0.2	_
Gain Variation over Temperature	_	dB/°C	_	0.009	_
Output Power	P _{IN} = 5.4 dBm, 4 GHz P _{IN} = 5.4 dBm, 6 GHz P _{IN} = 3.0 dBm, 8 GHz	dBm	17.5 17.5 15.0	20.5 20.5 18.0	_
Noise Figure	_	dB	_	5	_
Input Return Loss	_	dB	_	15	_
Output Return Loss	_	dB	_	15	_
P1dB	_	dBm	_	19	_
P3dB		dBm	_	22	_
OIP3	_	dBm	_	30	_
Phase Noise @ 100 Hz	4 GHz, P1dB, 100 Hz 1 KHz 10 KHz 1 MHz	dBc/Hz	_	148 160 165 175	_
Icq	_	mA	_	85	_

Maximum Operating Conditions

Parameter	Maximum
P _{IN}	12 dBm
V _{CC}	6 V
Icq	105 mA
Junction Temperature ^{5,6}	+130°C
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +150°C

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1A devices.

Absolute Maximum Ratings^{7,8}

Parameter	Absolute Maximum	
P _{IN}	20 dBm	
V _{CC}	6.5 V	
Icq	170 mA	
Junction Temperature ^{5,6}	+150°C	
Operating Temperature	-40°C to +85°C	
Storage Temperature	-40°C to +150°C	

- 5. Operating at nominal conditions with $T_J \le +150^{\circ} C$ will ensure MTTF > 1 x 10^6 hours.
- 6. Junction Temperature (T_J) = T_C + Θ jc * (V * I) Typical thermal resistance (Θ jc) = 24.0°C/W.
 - a) For $T_C = +25$ °C,

T_J = 40.1°C @ 6 V, 105 mA

b) For $T_C = +85^{\circ}C$,

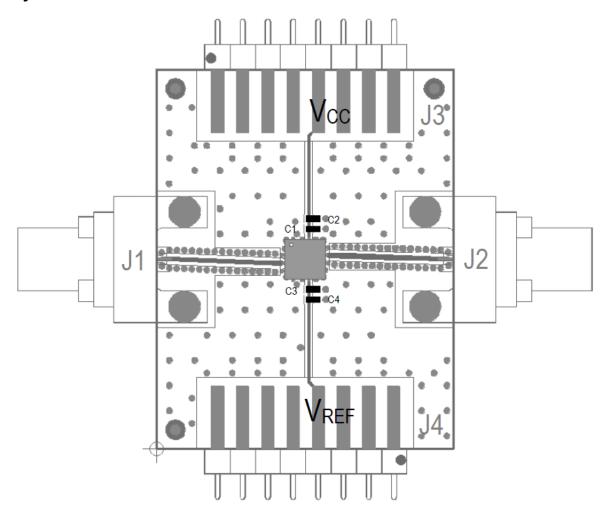
T_J = 100.1°C @ 6 V, 105 mA

- 7. Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.



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PCB Layout



Parts List

Part	Value	Case Style
C1,C3	100 pF	0402
C2,C4	0.1 μF	0402

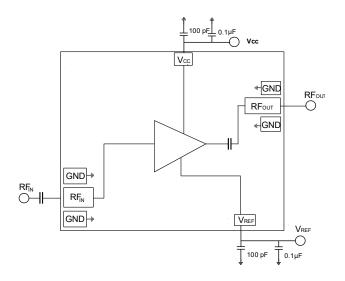
Evaluation PCB Specifications

Top Layer: 1 oz Copper Cladding, 0.034 mm thickness Dielectric Layer: Rogers RO4350B 0.245 mm thickness Bottom Layer: 1 oz Copper Cladding, 0.034 mm thickness Finished overall thickness: 0.313 mm



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Application Schematic



Operation

The technology is HBT; so, the turn-on and turn-off procedure is fairly simple.

To turn-on simply:

- 1. Apply +5 V to V_{CC}
- 2. Starting at 0 V, adjust V_{REF} for target I_{CC}

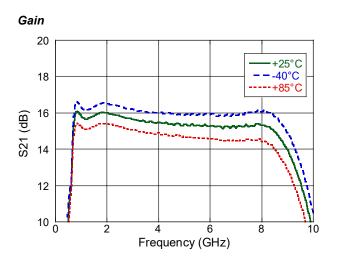
To turn-off:

- 1. Set V_{REF} to 0 V
- 2. Set V_{CC} to 0 V

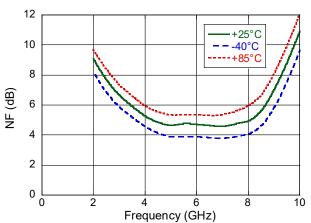


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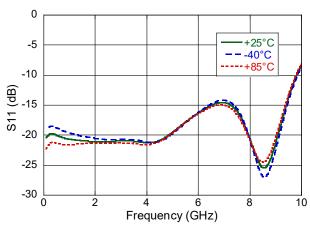
Typical Performance Curves: $V_{cc} = 5 \text{ V}$, $I_{cc} = 85 \text{ mA}$



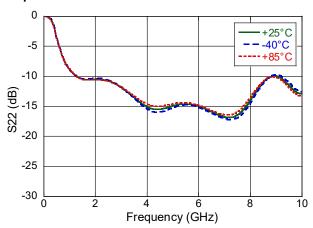
Noise Figure



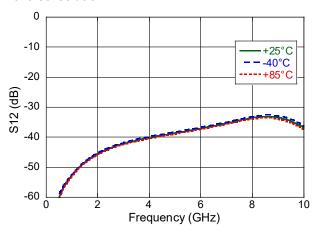
Input Return Loss



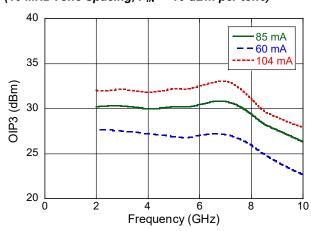
Output Return Loss



Reverse Isolation



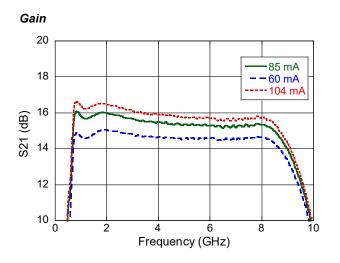
Output IP3 (10 MHz Tone Spacing, $P_{IN} = -10$ dBm per tone)





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Typical Performance Curves: V_{CC} = 5 V, 25°C

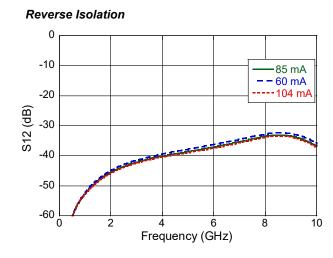


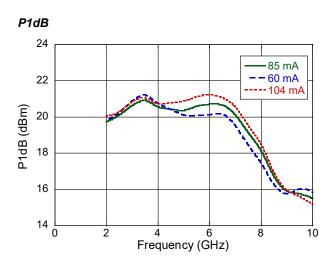
1nput Return Loss 0 -5 -10 -10 -15 -20 -25 -30 0 2 4 6 8 10

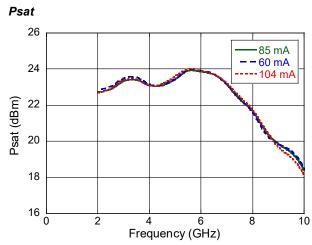
Frequency (GHz)

Output Return Loss 0 -5 -10 -10 -10 -25 -30 0 2 4 6 8 10

Frequency (GHz)



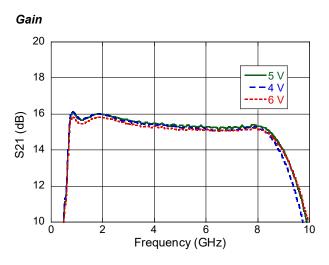


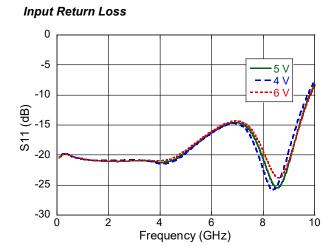


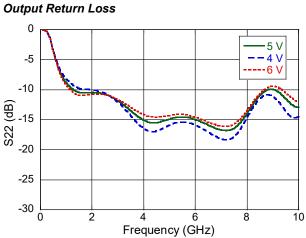


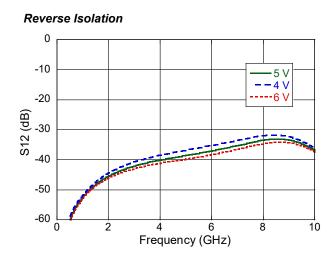
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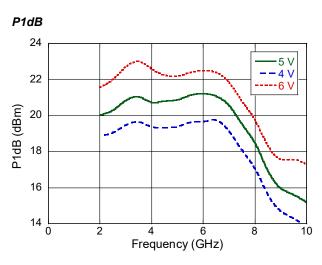
Typical Performance Curves: I_{CC} = 85 mA, 25°C

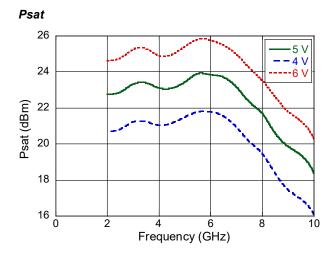












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Typical Performance Curves: I_{CC} = 85 mA, 25°C

Phase Noise @ 4 GHz, P1dB -140 -150 -160 Phase Noise @ 4 GHz, P1dB

1000

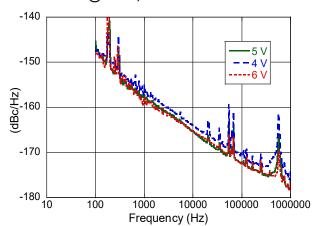
Frequency (Hz)

10000

100000

1000000

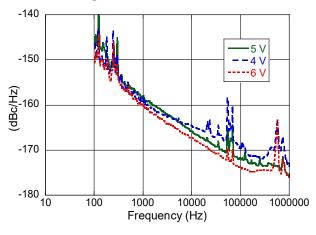
Phase Noise @ 4 GHz, P4dB



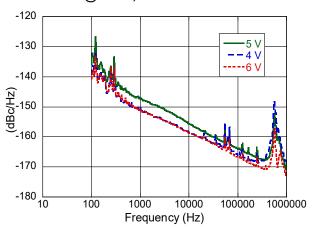


100

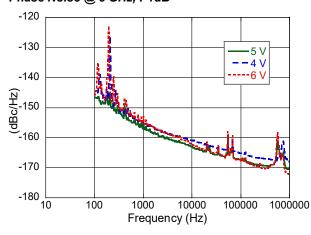
-180 L



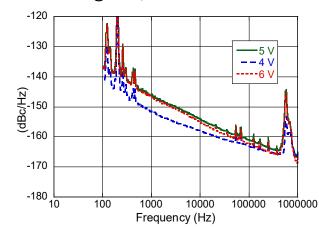
Phase Noise @ 6 GHz, P4dB



Phase Noise @ 8 GHz, P1dB



Phase Noise @ 8 GHz, P4dB



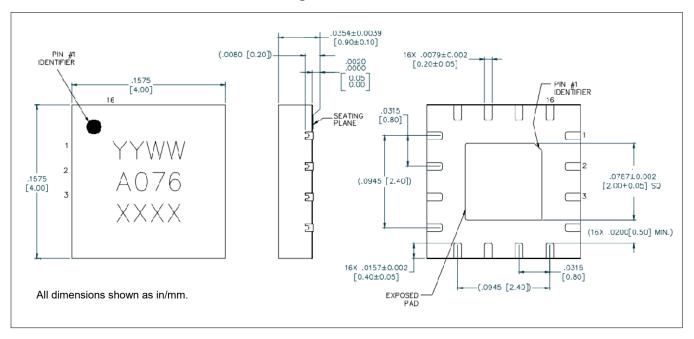
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Lead-Free 4 mm 16-Lead PQFN Package



[†] Reference Application Note S2083 for lead-free solder reflow recommendations. Meets JEDEC moisture sensitivity level 1 requirements. Plating is NiPdAuAg.